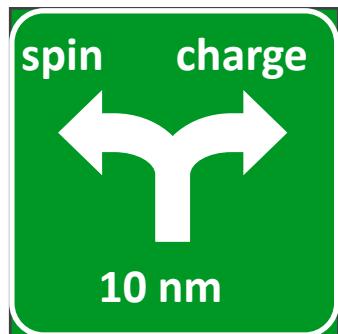
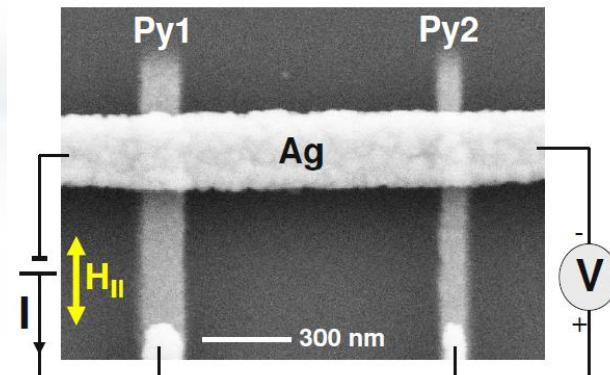


New Insights into Spin Relaxation from Pure Spin Currents



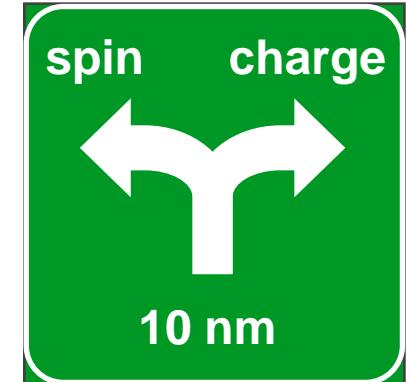
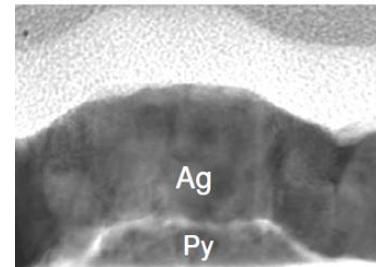
Axel Hoffmann



Materials Science Division
Argonne National Laboratory

Outline

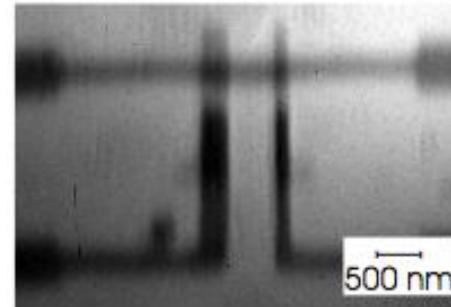
■ Why Pure Spin Currents?



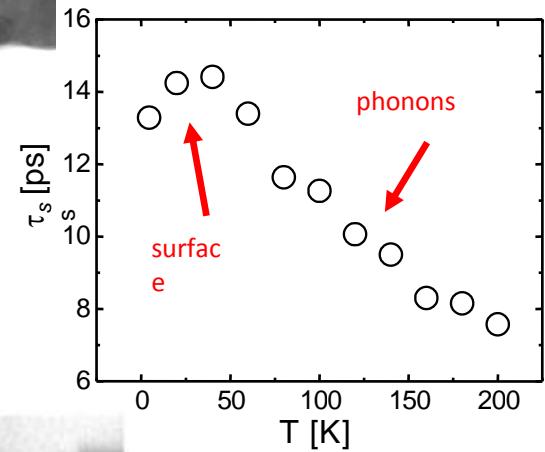
■ Interfacial Oxide

■ Surface Spin Relaxation

■ What about X-rays?



■ Conclusions

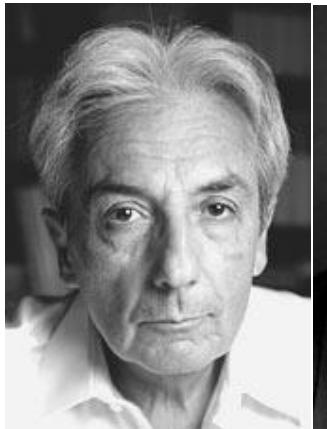


Spintronics

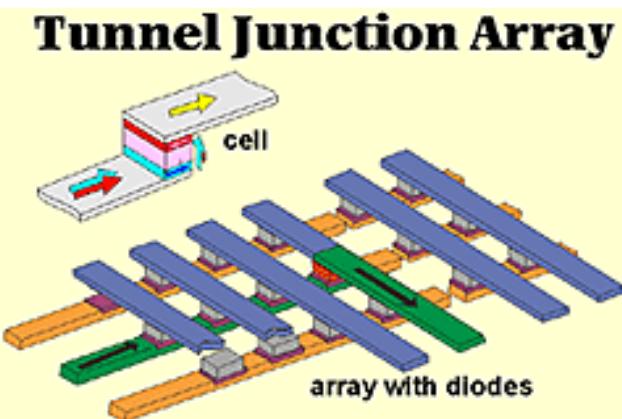
Putting



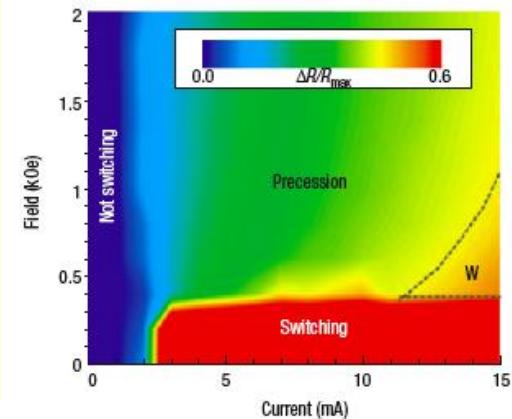
into Electronics



Nobel Prize



Novel Devices



New Physics

Recent Review: S. D. Bader and S. S. P. Parkin, Annu. Rev. Cond. Matter Phys. **1**, 71 (2010)

Charge vs. Spin Currents

Charge

$$\vec{j}_e = \frac{d}{dt} (q\vec{r})$$

$$\vec{j}_e = q\vec{v}$$

Spin

$$\vec{j}_s = \frac{d}{dt} (\sigma\vec{r})$$

$$\vec{j}_s = \sigma\vec{v} + \vec{\delta r}$$

Moving
Spins

Spin
Dynamics



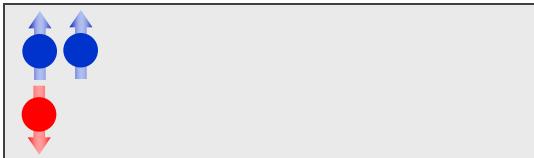
No Need for Moving Spin:
Potential for Low Power Dissipation!

J. Shi, et al., Phys. Rev. Lett. **96**, 076604 (2006).

Pure Spin Currents

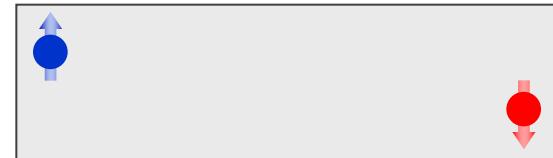
Spin polarized charge current

$$\begin{aligned} j_c &\neq 0 \\ j_s &\neq 0 \end{aligned}$$



$$\begin{aligned} j_c &= 0 \\ j_s &\neq 0 \end{aligned}$$

Pure spin current



BENEFITS

physics

applications

Direct insights into
spin-dependent physics

- role of spin orbit coupling
in spin transport
- role of spin in energy transfer
- spin-spin interactions

Eliminate undesirable
charge transport effects

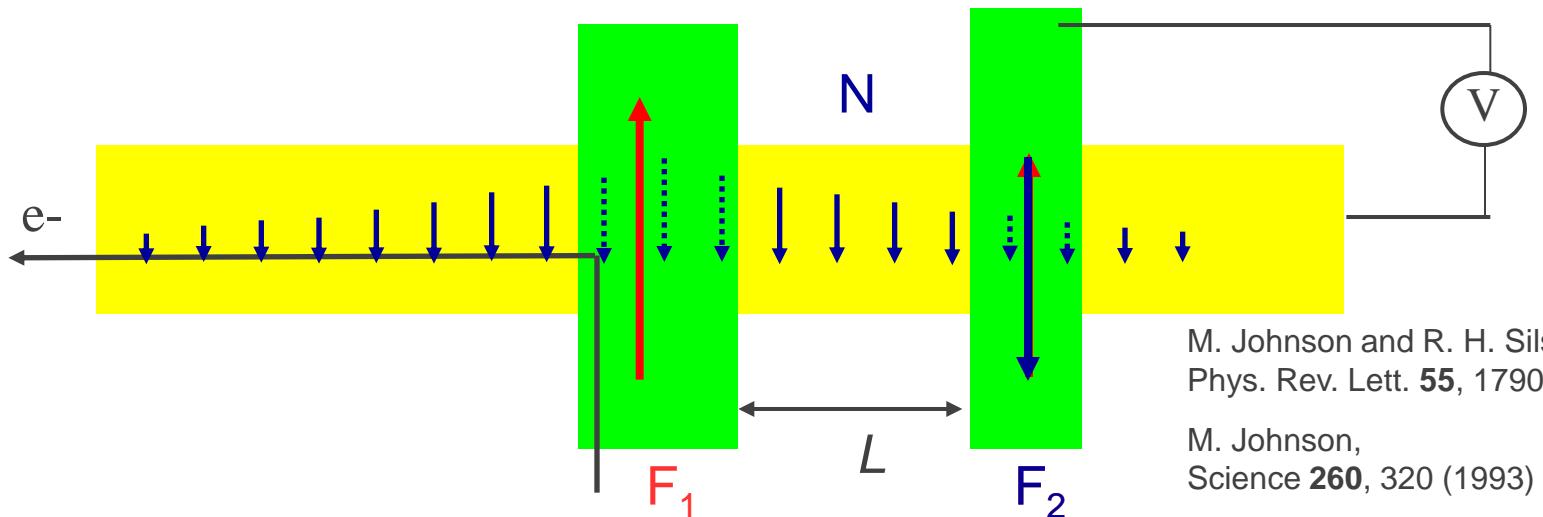
- heat
- noise
- Oersted fields



New Goal:

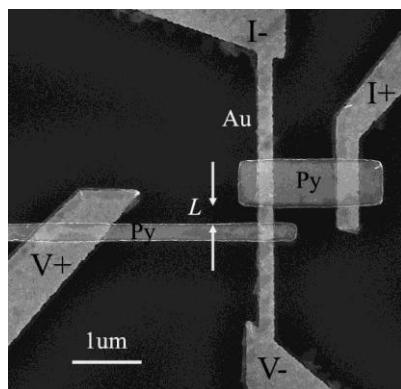
Take the
charge out of
Spintronics!

Pure Spin Currents: The Johnson Transistor



M. Johnson and R. H. Silsbee,
Phys. Rev. Lett. **55**, 1790 (1985)

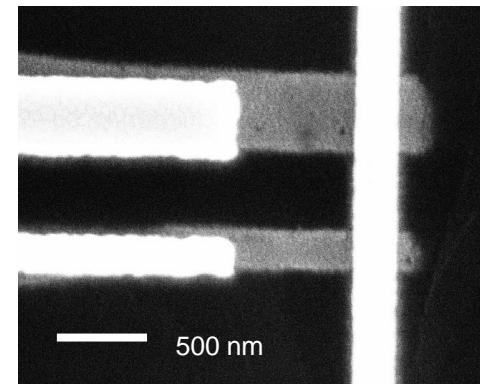
M. Johnson,
Science **260**, 320 (1993)



Au: $\lambda_s = 63 \pm 15$ nm (10 K)

Y. Ji *et al.*, Appl. Phys. Lett. **85**, 6218 (2004)

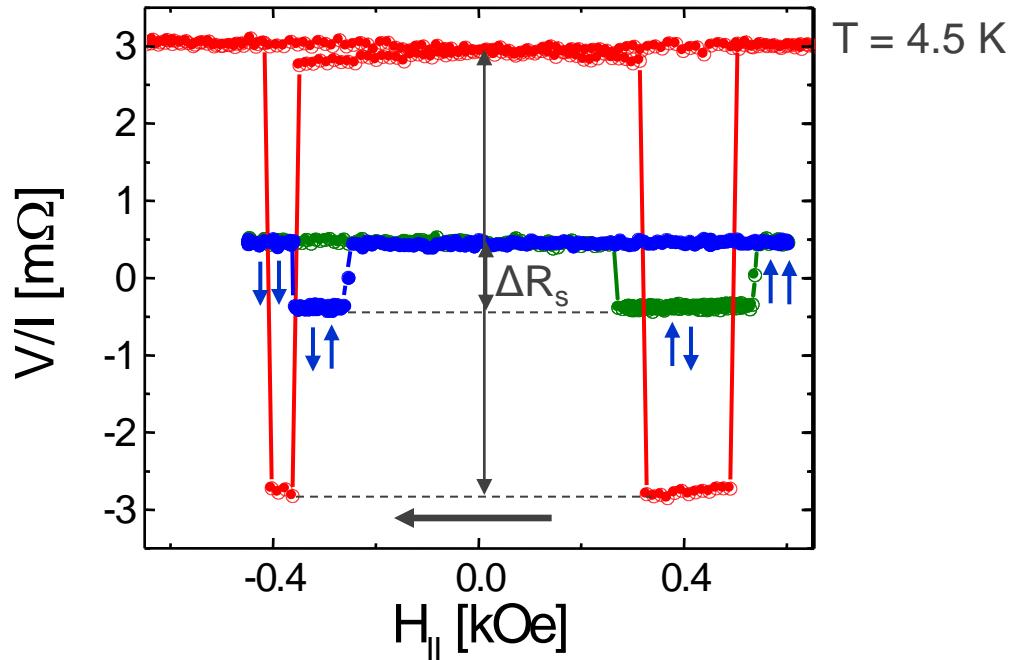
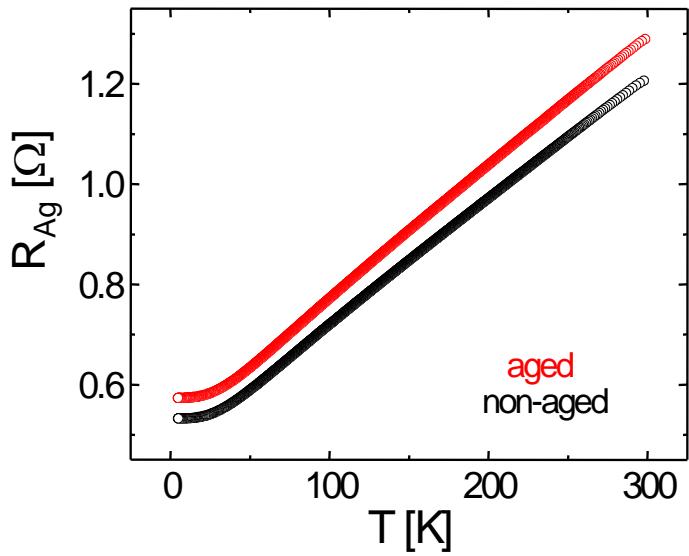
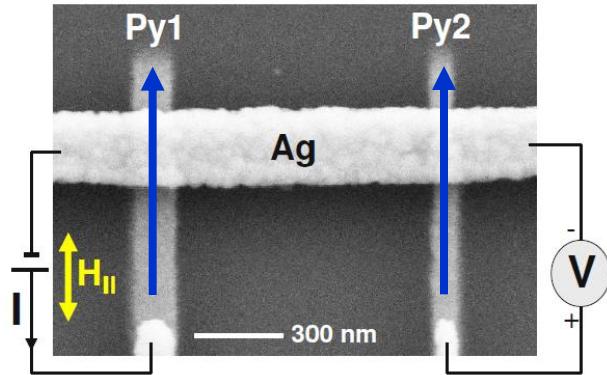
Our Early Work



Cu: $\lambda_s = 200 \pm 20$ nm (10 K)

Y. Ji *et al.*, Appl. Phys. Lett. **88**, 052509 (2006)

Py/Ag Non-Local Spin Valve



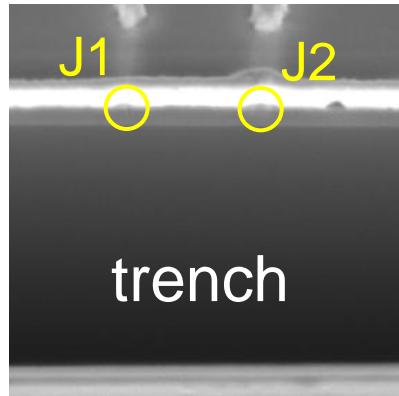
$$\Delta R_s = 0.9 \text{ m}\Omega \xrightarrow{\text{after 2 weeks in air}} \Delta R_s = 5.9 \text{ m}\Omega$$

$$\boxed{\Delta R_s = \frac{P^2 \rho \lambda_s}{A} \exp\left(-\frac{L}{\lambda_s}\right)}$$

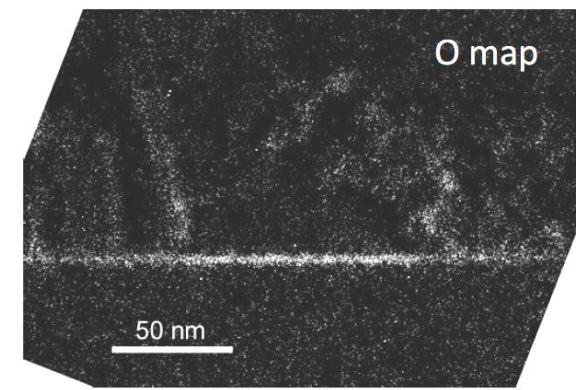
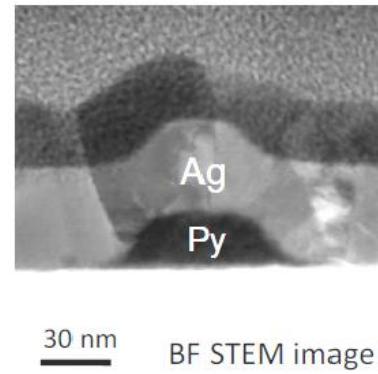
G. Mihajlović *et al.*, Appl. Phys. Lett. **97**, 112502 (2010)

Origin of Enhanced ΔR_s

FIB sliced LSV

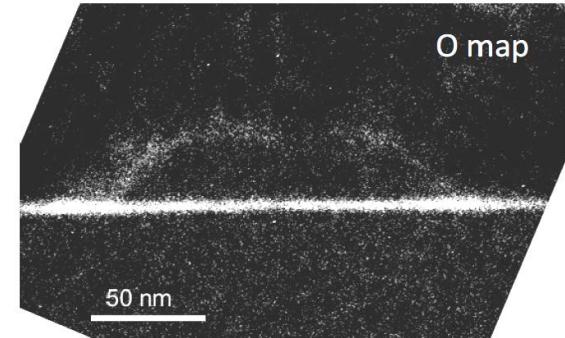
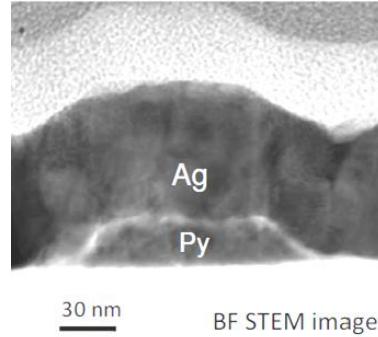


TEM of a non-aged sample



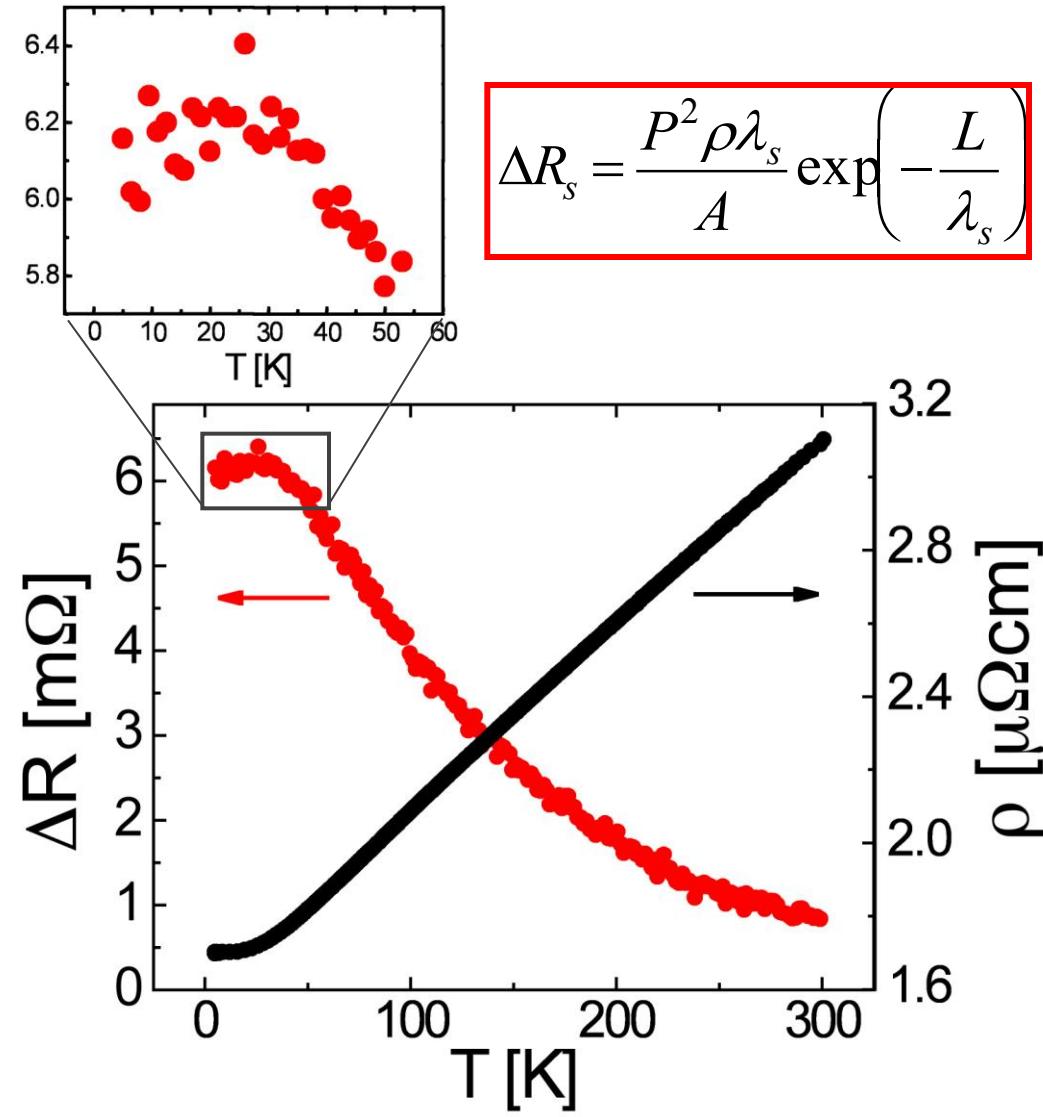
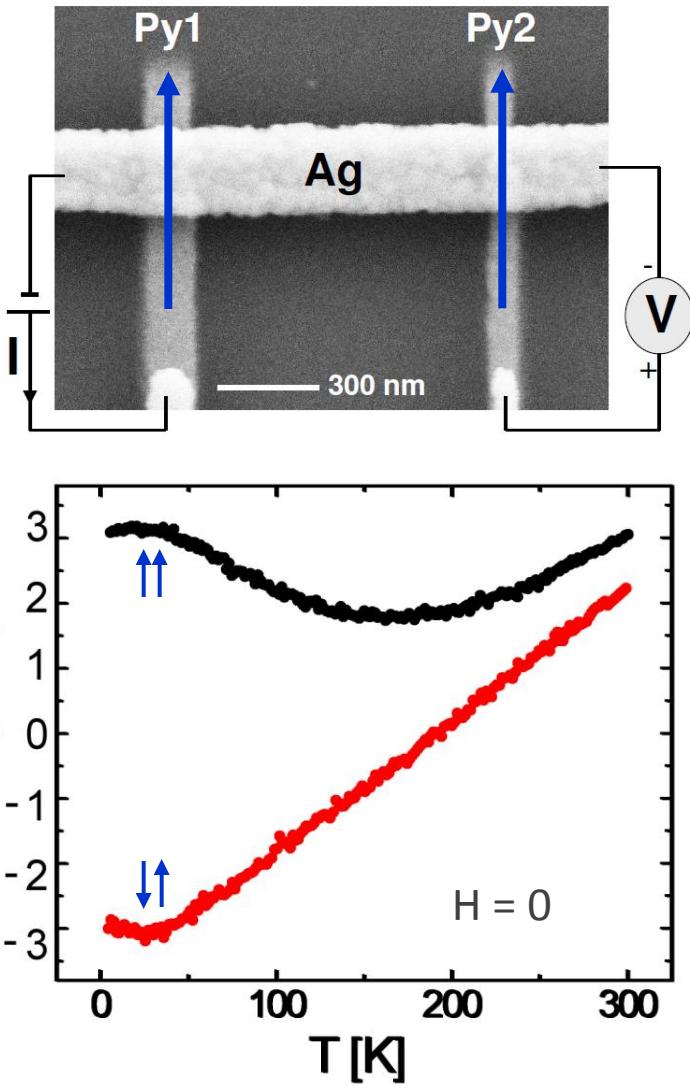
Thin layer of O-rich compound observed at Py-Ag interface in aged samples

TEM of an aged sample

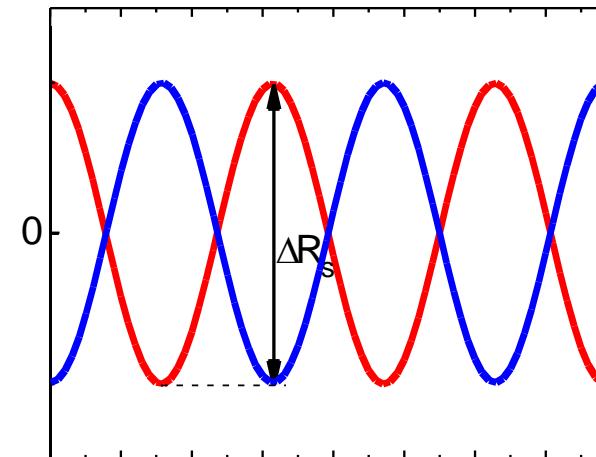
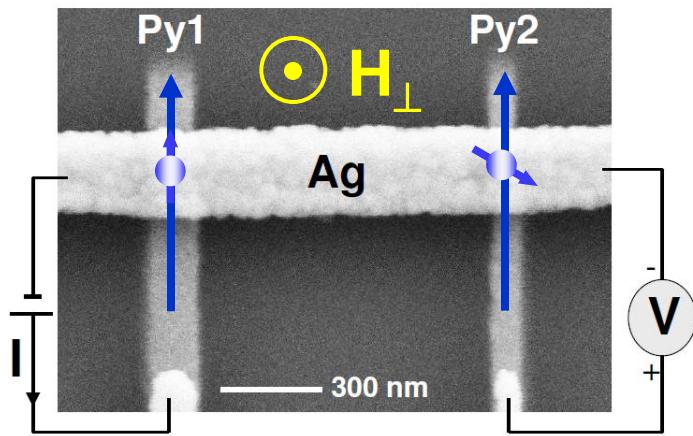


Higher interface resistance → Better spin injection efficiency

Temperature Dependence of Spin Signal



Hanle Effect in Lateral Spin Valves



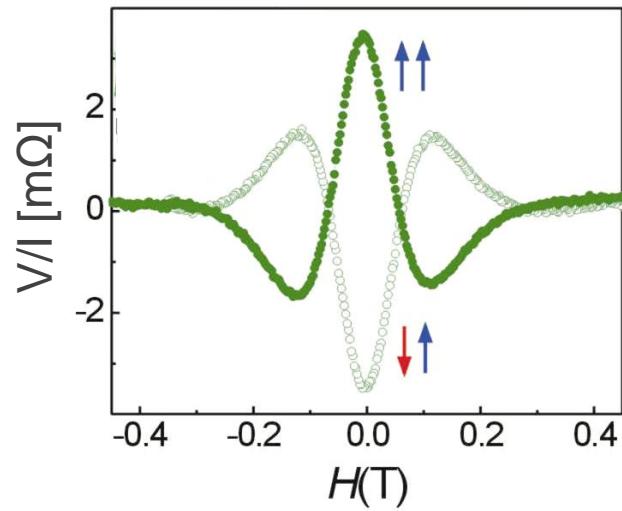
Spin diffusion + Spin relaxation



Spin dephasing

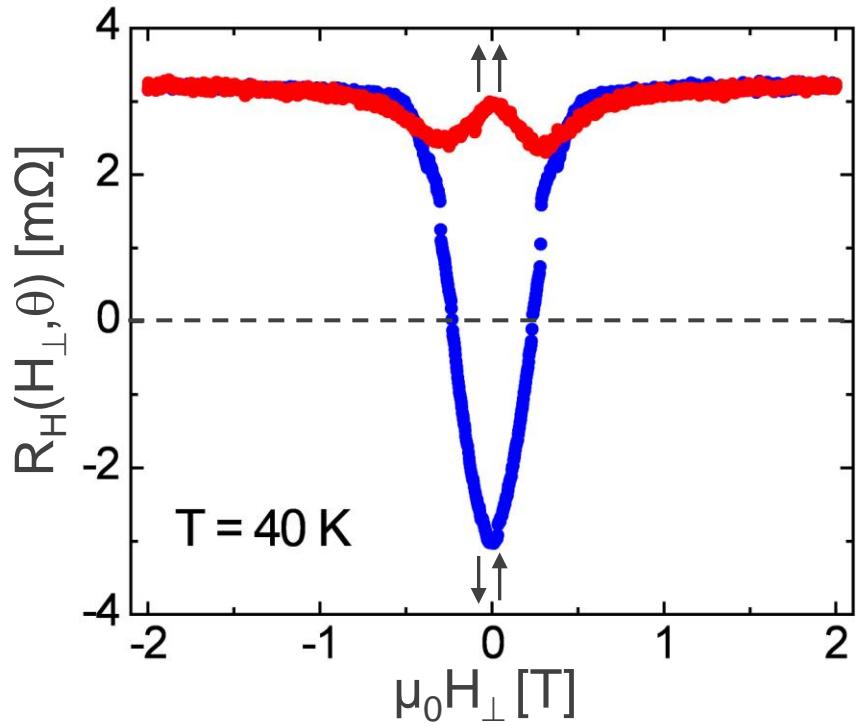
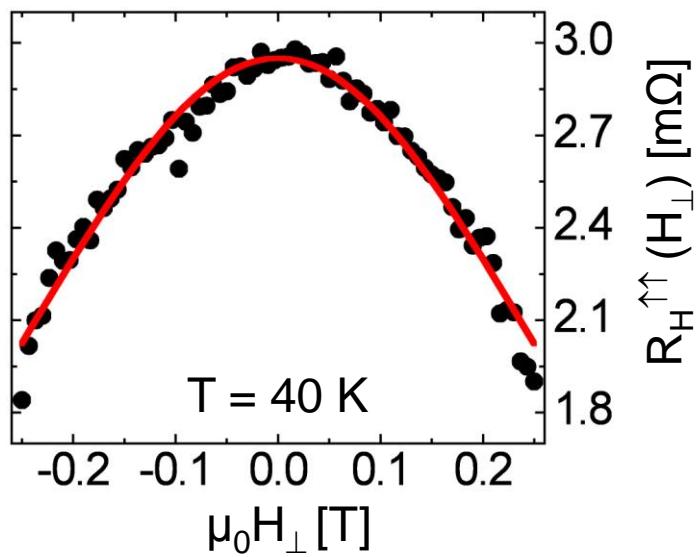
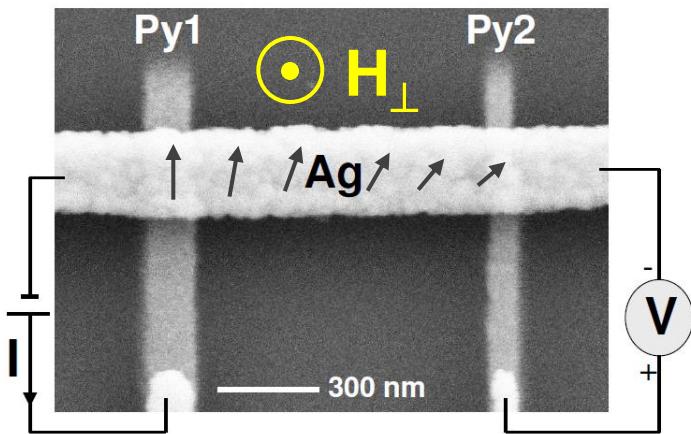
$$R_H^{\uparrow\downarrow}(H_{\perp}) = \frac{P^2 \rho D}{A} \int_0^{\infty} \mathcal{P}(t) \cos(\omega_L t) \exp\left(-\frac{t}{\tau_s}\right) dt$$

P and τ_s from Hanle curves



Jedema et al., *Nature* (2002)
Valenzuela & Tinkham, *Nature* (2006)

Hanle Effect in Py/Ag Lateral Spin Valves

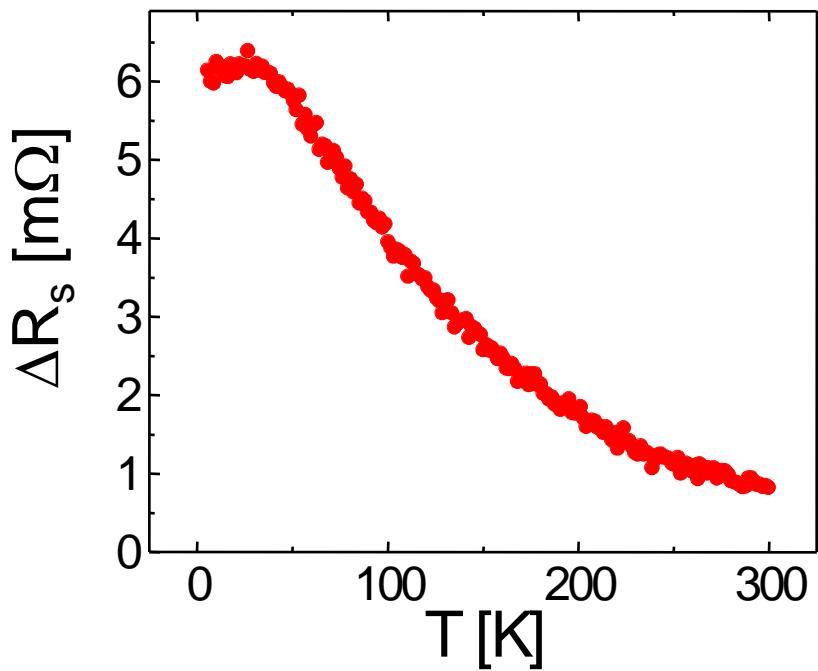


$$P = 0.207$$

$$\tau_s = 14.4 \text{ ps}$$

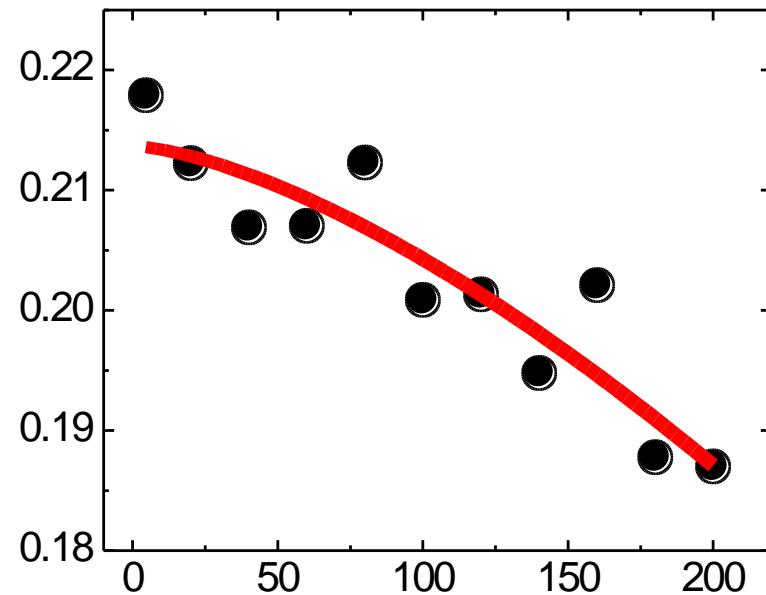
$$\lambda_s = 564 \text{ nm}$$

T -Dependence of Injection Polarization



P decreases with T
due to thermally excited spin waves

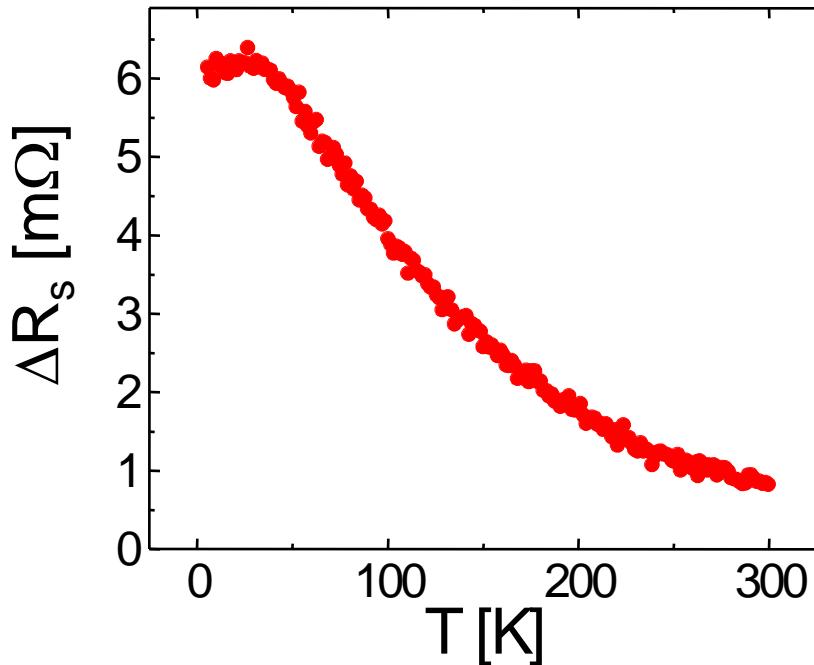
$$\Delta R_s = \frac{P^2 \rho \lambda_s}{A} \exp\left(-\frac{L}{\lambda_s}\right)$$



$$P(T) = P_0(1 - \alpha T^{3/2})$$

$$P_0 = 0.214 \pm 0.003$$
$$\alpha = (4.0 \pm 0.6) \times 10^{-5} \text{ K}^{-3/2}$$

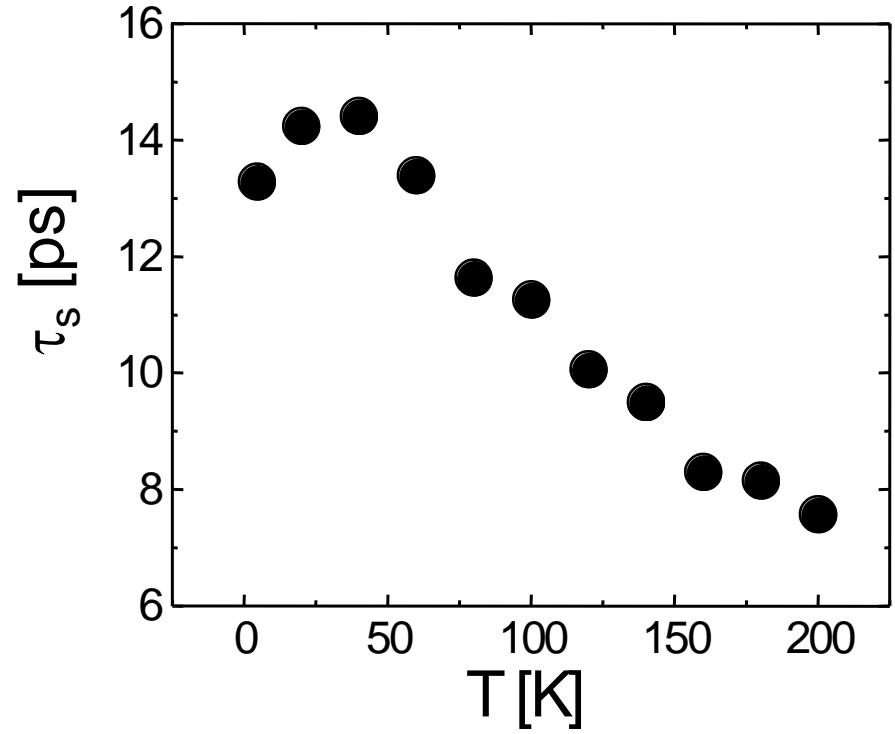
T -Dependence of Spin Relaxation Time



$$\lambda_s = \sqrt{D\tau_s}$$

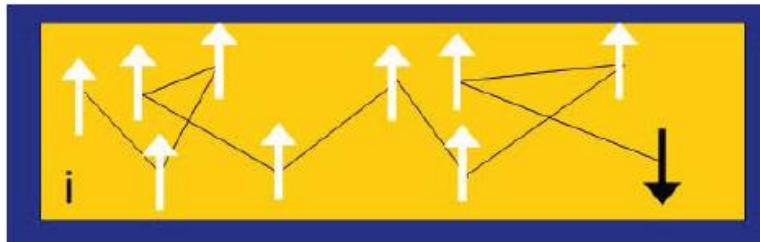
ΔR_s decreases
due to decreasing τ_s

$$\boxed{\Delta R_s = \frac{P^2 \rho \lambda_s}{A} \exp\left(-\frac{L}{\lambda_s}\right)}$$



T-Dependence: What about Elliott-Yafet?

momentum relaxation + SOC = spin relaxation



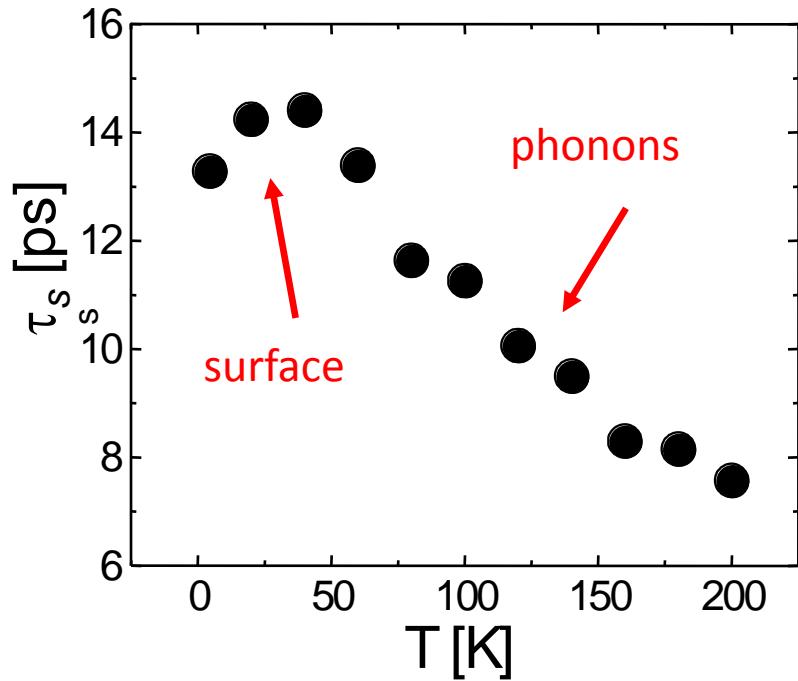
$$\tau_s \propto \tau_e$$

confirmed many times
in bulk metals

$$\frac{1}{\tau_e} = \frac{1}{\tau_e^{ph}} + \frac{1}{\tau_e^{imp}} + \frac{1}{\tau_e^S}$$

$$\frac{1}{\tau_s} = \frac{\mathcal{E}_{ph}}{\tau_e^{ph}} + \frac{\mathcal{E}_{imp}}{\tau_e^{imp}} + \frac{\mathcal{E}_S}{\tau_e^S}$$

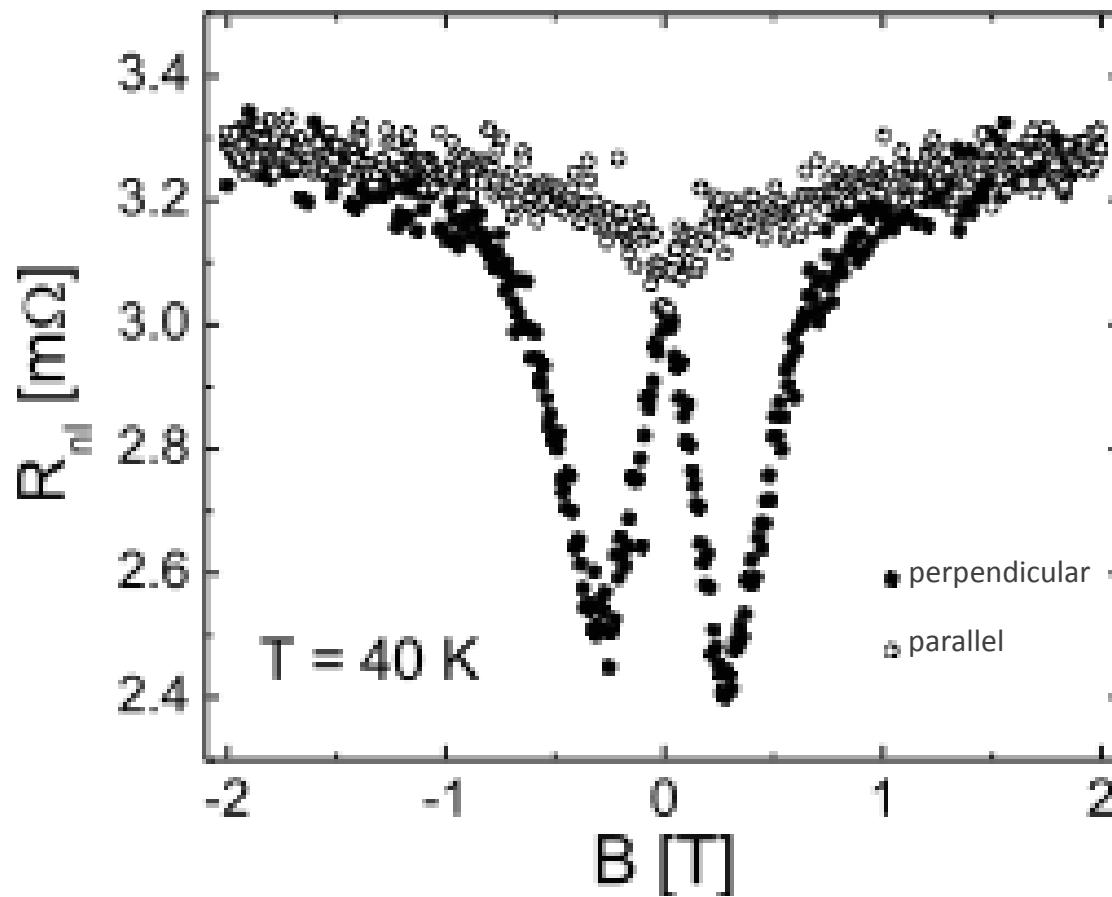
$\propto 1/T$ $\propto T$



our samples: $\lambda_e < d$ \rightarrow

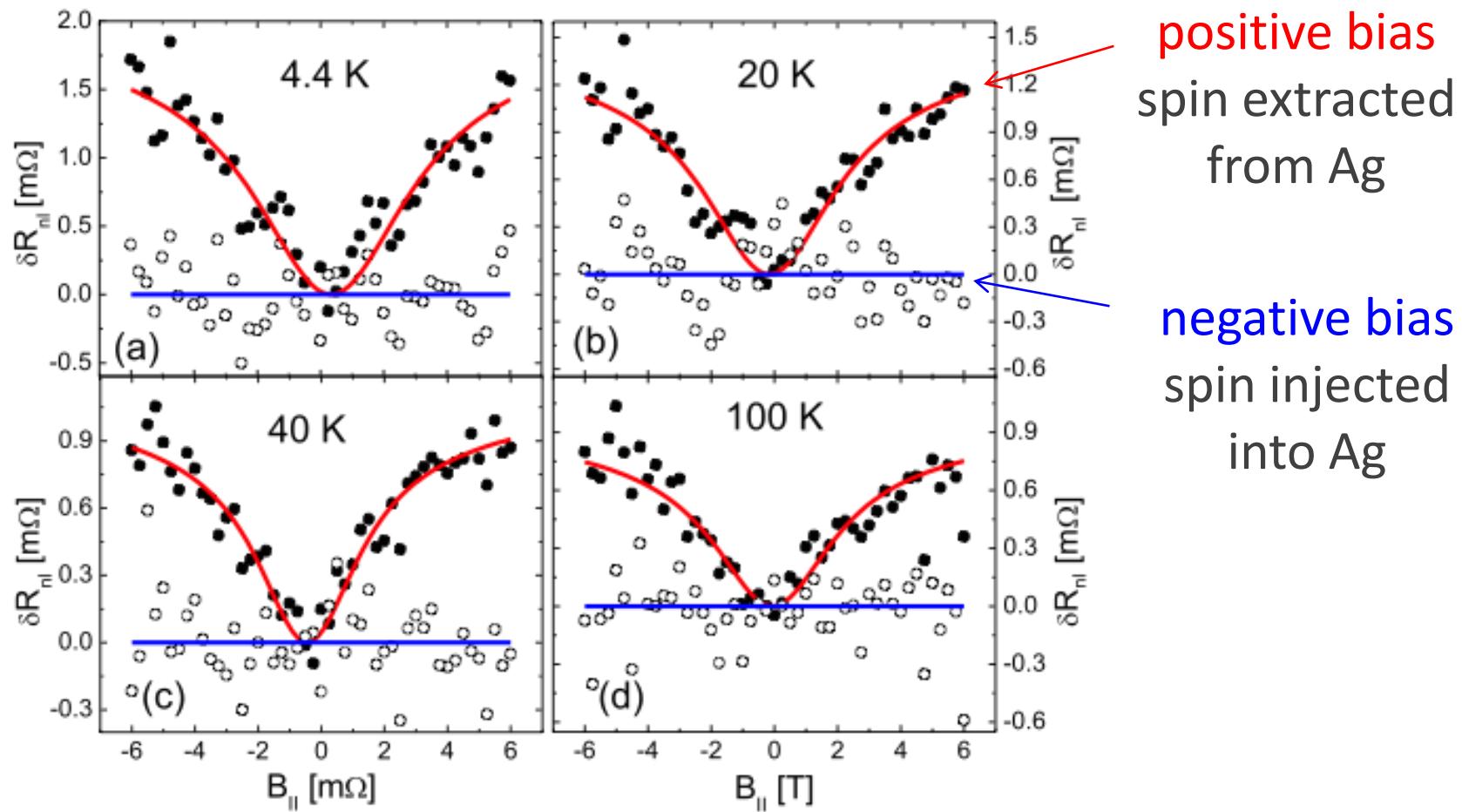
$$\tau_e^S \propto d^2 / D_B \propto 1 / \tau_e^B \propto T$$

Magnetic Field Dependence?



Spin signal increases with field!

Only for Positive Bias!

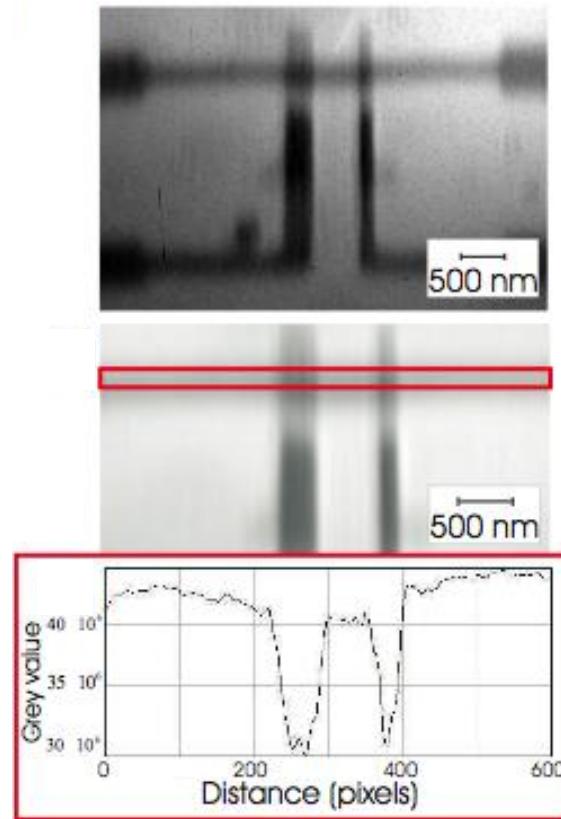


Polarity of spin accumulation matters!
Maybe magnetic impurity scattering is responsible

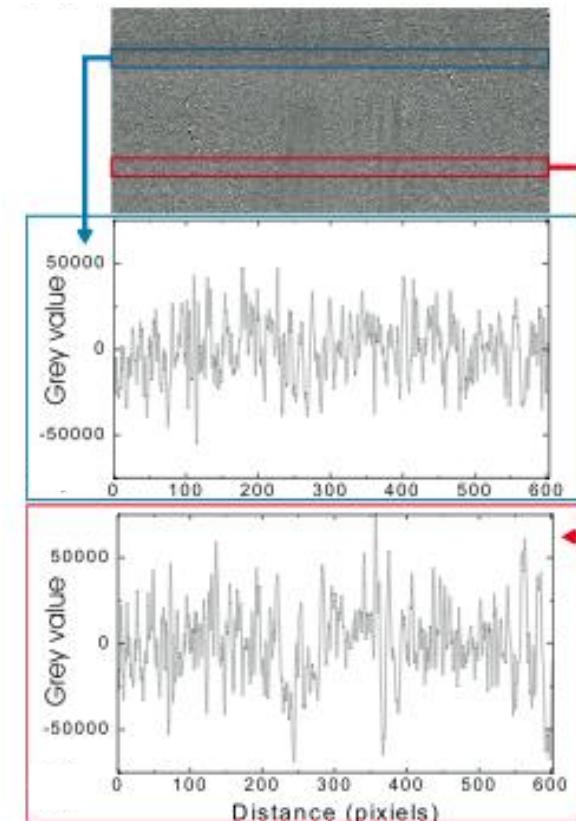
Can we Image Spin Accumulation Directly?

How about X-ray Dichroism?

Image at Cu L-edge



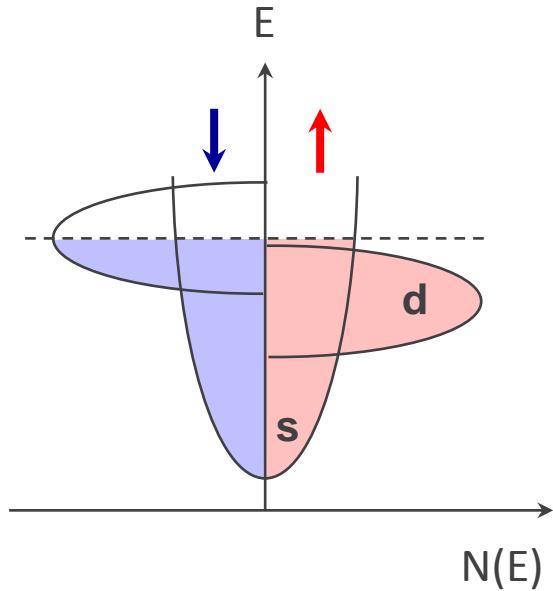
Magnetic Difference Images



Mosendz *et al.*, Phys. Rev. B **80**, 104439 (2009)

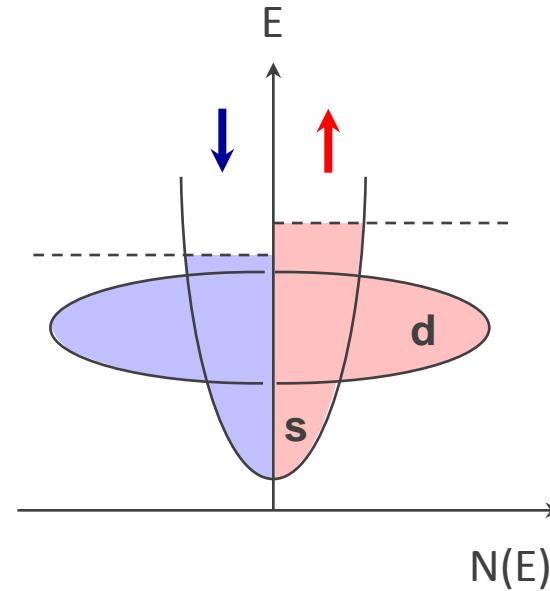
Is There Any Hope for X-rays?

Ferromagnet
(i.e., typical TM)



Contrast due to
different density of states at
Fermi-level

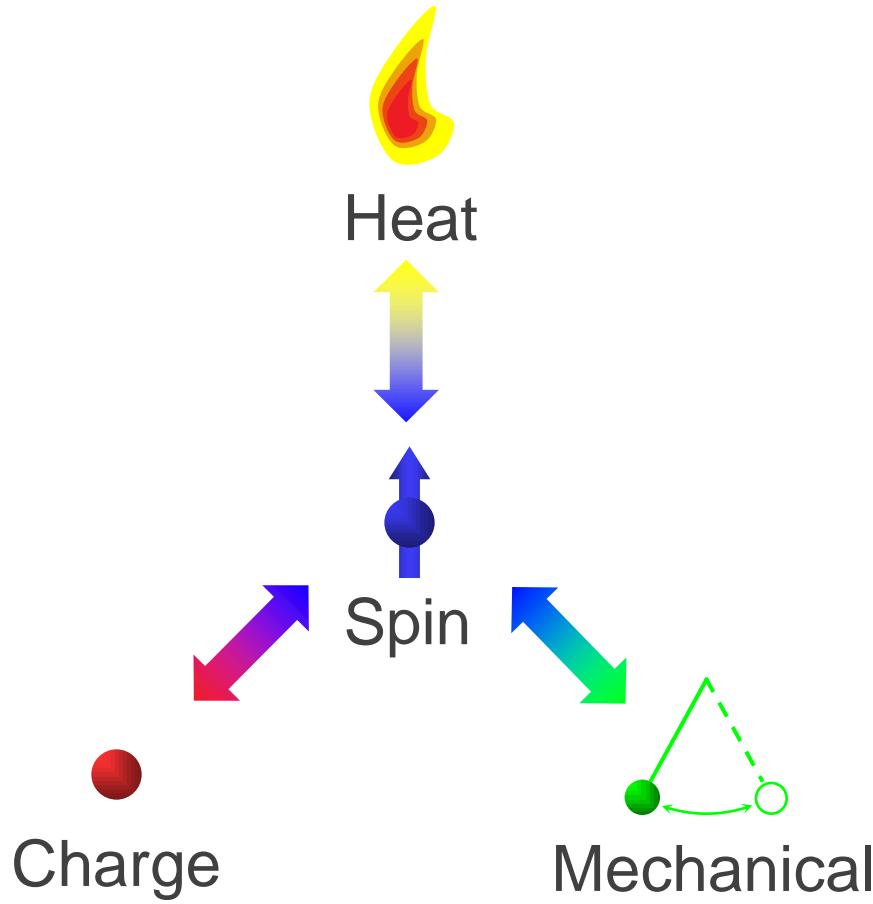
Spin Accumulation



Contrast due to
spin-splitting?
Well below 1 meV!

Spin Mediated Energy Conversions

Spin Seebeck \leftrightarrow Spin Peltier



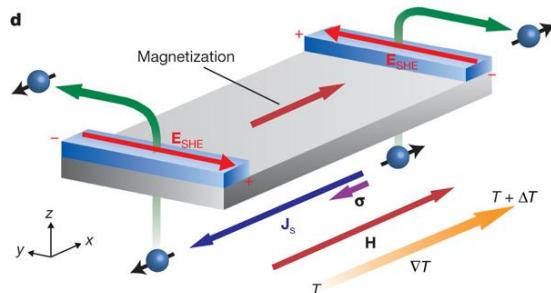
Spin Torque \leftrightarrow EMF from Spin Dynamics

Einstein-de Haas \leftrightarrow Barnett

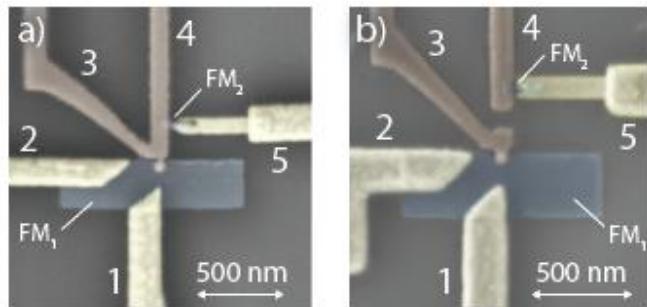


Spin Caloritronics

Spin Seebeck



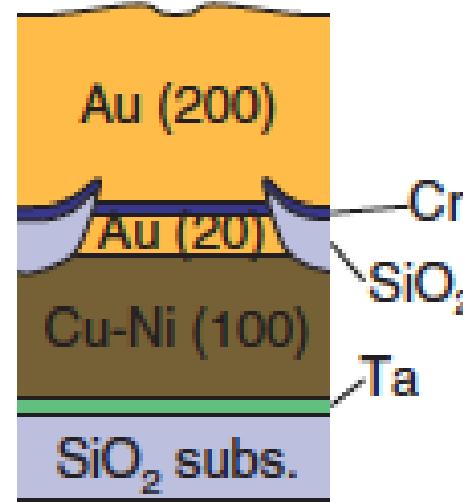
K. Uchida *et al.*, Nature **455**, 778 (2008)



F. L. Bakker *et al.*, Phys. Rev. Lett. **105**, 136601 (2010)

spin waves vs. diffusion?

Spin Peltier



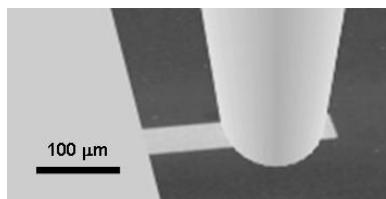
A. Sugihara *et al.*, Appl. Phys. Express **3**, 065204 (2010)

Giant Peltier
more than 160 K cooling!

Magnetomechanical Coupling

Einstein-De Haas in MEMS

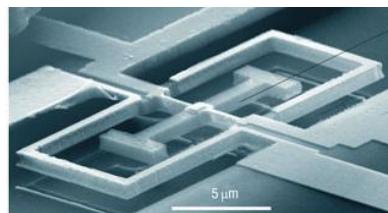
NIST



*Moreland et al.,
APL 2006*

Measure
EdH-Effect with μ -
cantlever

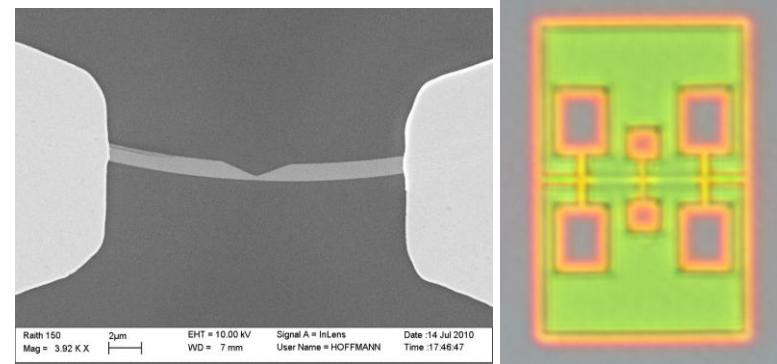
Boston University



*Mohanty et al.,
Nature Nanotechn. 2008*

Measure
electric spin injection with
torsional oscillator

Coupled Magneto-Mechanical Dynamics



NEWS & VIEWS

NANOMECHATRONICS

A new twist on a classic experiment

The interplay between angular momentum, electron spin and magnetism at the nanoscale could have applications in spintronics, transducers and actuators, as well as fundamental research.

Kovalev Nature Nanotechn. 2008

Domain
Wall

Torsional
MEMS

Both about 20 MHz!

Thanks to

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Dan Schreiber, Yuzi Liu, and Amanda Petford-Long
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Sigurður I. Erlingsson

Reykjavik University

Mi-Young Im and Peter Fischer
Lawrence Berkeley National Laboratory

\$\$\$ Financial Support \$\$\$
DOE-BES

Conclusions

- Lateral Spin Valve
 - Enable Pure Spin Currents
- Permalloy/silver lateral spin valves
 - Ambient exposure results in enhanced spin injection
- Temperature dependence of spin signal
 - Surface spin relaxation is significantly larger than bulk
- Magnetic field dependence
 - Possibly due to magnetic impurities

